

AM2302N-T1-PF-VB Datasheet N-Channel 20 V (D-S) MOSFET

PRODUC	CT SUMMARY		
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^e	Q _g (Typ.)
	0.022 at V _{GS} = 4.5 V	6 ^a	
20	0.028 at V _{GS} = 2.5 V	6 ^a	8.8 nC
	0.039 at V _{GS} = 1.8 V	5.6	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

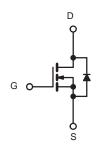


ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications





N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	IGS 1A - 25 C,			1114
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	v
	T _C = 25 °C		6 ^a	
Continuous Drain Current (T = 150 °C)	T _C = 70 °C] ,	5.1	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	- I _D	5 ^{b, c}	
	T _A = 70 °C		4 ^{b, c}	Α
Pulsed Drain Current	•	I _{DM}	20	
Ocationary Comments Disable Comments	T _C = 25 °C		1.75	
Continuous Source-Drain Diode Current	T _A = 25 °C	- I _S	1.04 ^{b, c}	
	T _C = 25 °C		2.1	
Marrian na Damar Dissipation	T _C = 70 °C] ,	1.3	۱۸/
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b, c}	W
	T _A = 70 °C		0.8 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RA	TINGS				
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	80	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	60] 0,00

Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 125 $^{\circ}\text{C/W}.$
- e. Based on T_C = 25 °C.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static			l .			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	V _{DS} /T _J		25		m\//º
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.6		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.45		1.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
		V _{DS} = 20 V, V _{GS} = 0 V			1	<u> </u>
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C			10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			Α
	, ,	$V_{GS} = 4.5 \text{ V}, I_D = 5.0 \text{ A}$		0.022		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.7 \text{ A}$		0.028		Ω
		$V_{GS} = 1.8 \text{ V}, I_D = 4.3 \text{ A}$		0.039		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5.0 A		24		S
Dynamic ^b				L		
Input Capacitance	C _{iss}			865		
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		105		pF
Reverse Transfer Capacitance	C _{rss}	20		55		
		V _{DS} = 10 V, V _{GS} = 5 V, I _D = 5.0 A		12	18	
Total Gate Charge	Q_g			8.8	14	-
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.0 \text{ A}$		1.1		nC
Gate-Drain Charge	Q _{gd}	20 00		0.7		
Gate Resistance	R _g	f = 1 MHz	0.5	2.4	4.8	Ω
Turn-On Delay Time	t _{d(on)}			8	16	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		17	26	ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 4$ A, V_{GEN} = 4.5 V, R_g = 1 Ω		31	47	
Fall Time	t _f			8	16	
Turn-On Delay Time	t _{d(on)}			5	10	115
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		13	20	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 4$ A, $V_{GEN}=5$ V, $R_g=1$ Ω		21	32	
Fall Time	t _f			6	12	
Drain-Source Body Diode Characteristic	s		l	I.		
Continuous Source-Drain Diode Current	Is	T _C = 25 °C			1.75	
Pulse Diode Forward Current	I _{SM}				20	A
Body Diode Voltage	V _{SD}	I _S = 4 A, V _{GS} = 0 V		0.75	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			12	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 4 4 4U/4 400 1/ T 07 00		5	10	nC
Reverse Recovery Fall Time	t _a	$I_F = 4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		7		
Reverse Recovery Rise Time	t _b			5		ns

Notes:

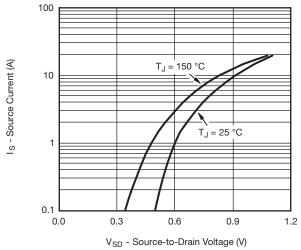
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

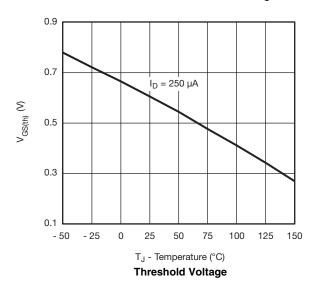


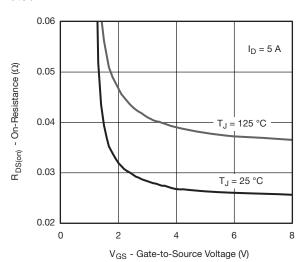






Source-Drain Diode Forward Voltage

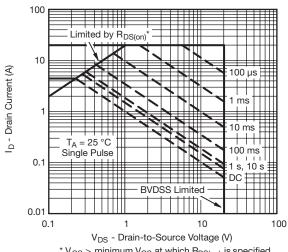




On-Resistance vs. Gate-to-Source Voltage



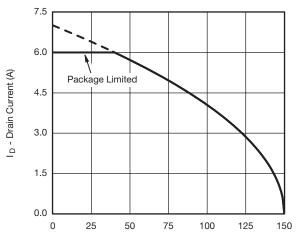
Single Pulse Power (Junction-to-Ambient)



 * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

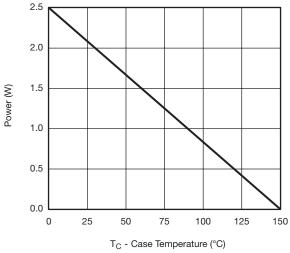
Safe Operating Area, Junction-to-Ambient



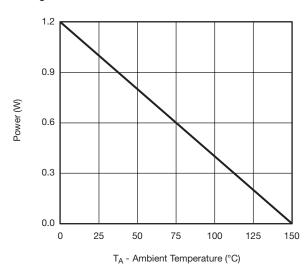


T_C - Case Temperature (°C)

Current Derating*



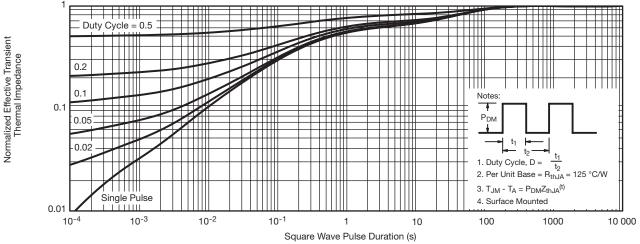




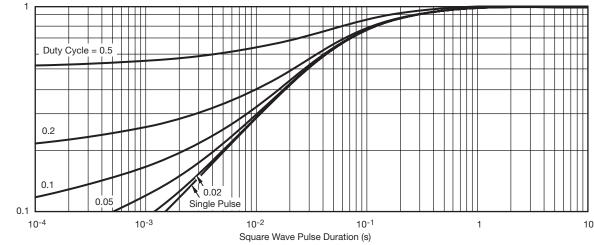
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.







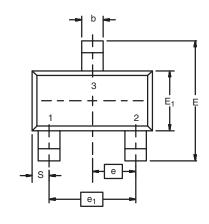


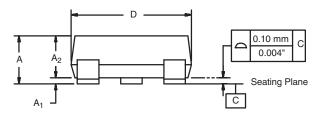
Normalized Thermal Transient Impedance, Junction-to-Foot

Normalized Effective Transient Thermal Impedance



SOT-23 (TO-236): 3-LEAD







Dim	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	i Ref	
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	

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DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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